

1000V 8A N-Channel Enhancement Mode Power MOSFET

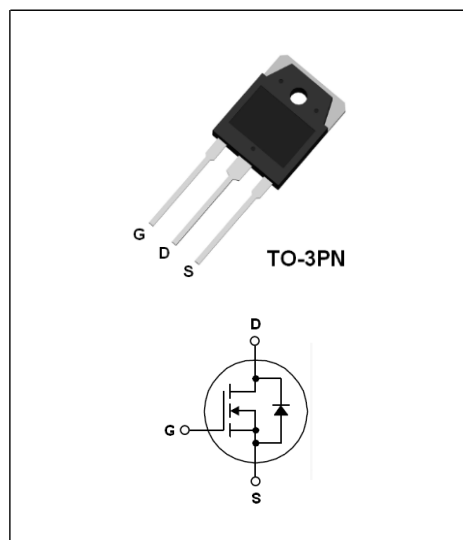
Description

The AKQA8N100 is an N-Channel enhancement mode power MOSFET which using proprietary planar stripe and DMOS technology.

This MOSFET has low static on-resistance and high avalanche energy strength. This device provide excellent switching performance for UPS,DC-DC converters and AC-DC power supply.

Features

- Low on-Resistance: $R_{DS(on)}=1.135\Omega(\text{typ.})$
- Special Process Technology for high ESD Capability
- 100% Avalanche Test
- Good Stability and Uniformity with High E_{AS}



Applications

- UPS Applications
- DC-DC Converters and AC-DC Power Supply

Absolute Maximum Ratings @ $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain to Source Voltage	1000	V
V_{GSS}	Gate to Source Voltage	± 30	V
I_D	Drain Current	$T_C=25^\circ\text{C}$	8
		$T_C=100^\circ\text{C}$	5
I_{DM}	Pulsed Drain Current (Note1)	32	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	225
	Derate above 25°C		1.78
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	890	mJ
T_J	Operating Junction Temperature Range	-55~+150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55~+150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{th(J-C)}$	Thermal Resistance, Junction to case	0.55	$^\circ\text{C}/\text{W}$
$R_{th(J-A)}$	Thermal Resistance, Junction to Ambient	40	$^\circ\text{C}/\text{W}$

Electrical Characteristics @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	1000	-	-	V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	3.0	4.085	5	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=4A$	-	1.135	-	Ω
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=1000V, V_{GS}=0V$	-	-	10	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	± 100	nA

D-S Diode Characteristics and Maximum Rating @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Maximum Drain to Source Diode Forward Current		-	-	8	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS}=0V, I_S=8A$	-	0.838	-	V
t_{rr}	Reverse Recovery Time	$V_{GS}=0V, I_S=8A,$	-	0.6	-	us
Q_{rr}	Reverse Recovery Charge	$di/dt=-100A/us$	-	5.1	-	μC

Switching Characteristics @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$I_D=8A,$ $V_{DD}=500V,$ $R_G=25\Omega$ (Note 3)	-	48	109	ns
t_r	Rising Time		-	95	198	ns
$t_{d(off)}$	Turn-off Delay Time		-	123	252	ns
t_f	Falling Time		-	77	168	ns
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=25V,$ $f=1.0MHz$	-	-	3200	pF
C_{oss}	Output Capacitance		-	-	255	pF
C_{riss}	Reverse Transfer Capacitance		-	-	23	pF
Q_g	Total Gate Charge	$I_D=8A,$ $V_{DS}=800V$ $V_{GS}=10V$ (Note 3)	-	53	-	nC
Q_{gs}	Gate to Source Charge		-	12	-	nC
Q_{gd}	Gate to Drain Charge		-	24	-	nC

Note:

1. Repetitive rating: pulse-width limited by maximum junction temperature
2. $L=5mH, V_{DD}=100V, V_G=10V, @T_C=25\text{ }^\circ\text{C}$
3. Essentially independent of operating temperature typical characteristics

Typical Performance Characteristics

Fig. 1. Typical on-Region Characteristics

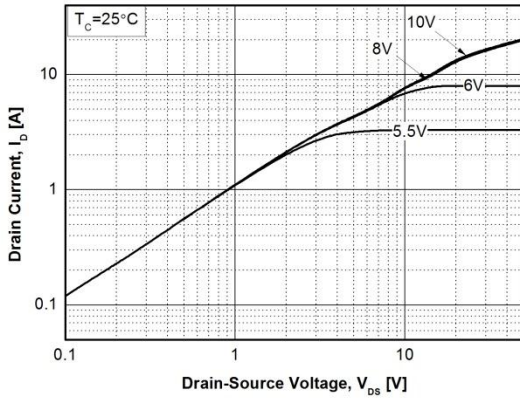


Fig. 2. Typical Transfer Characteristics

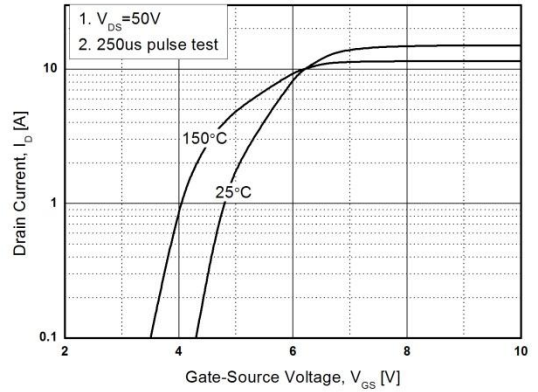


Fig. 3. Static on-Resistance vs. I_D

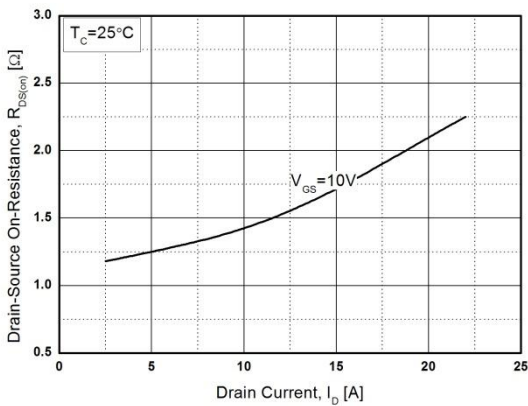


Fig. 4. Body Diode Forward Voltage vs. I_{DR}

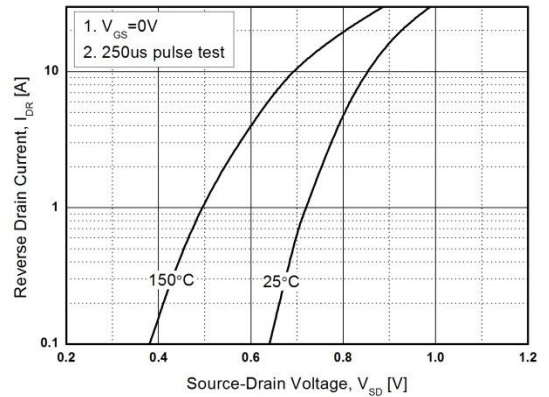


Fig. 5. Capacitance Characteristics

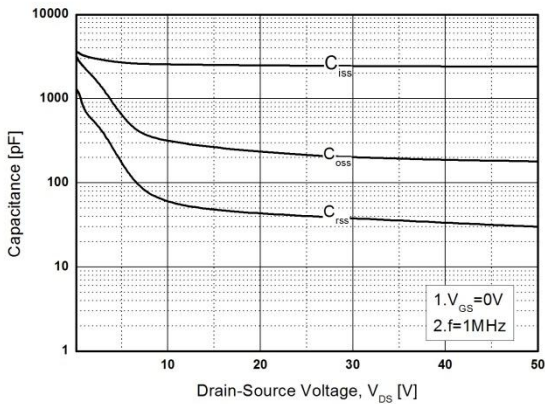
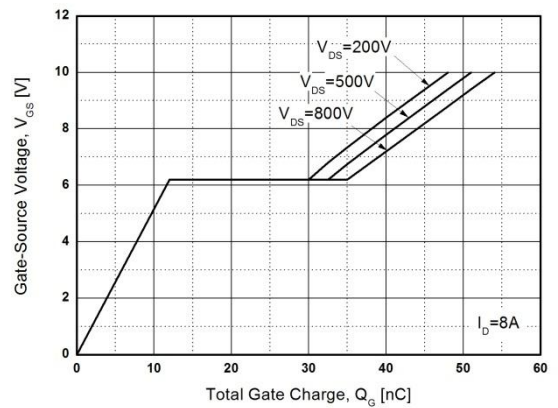


Fig. 6. Gate Charge Characteristics



Typical Performance Characteristics

Fig. 7. Breakdown Voltage vs. Temperature

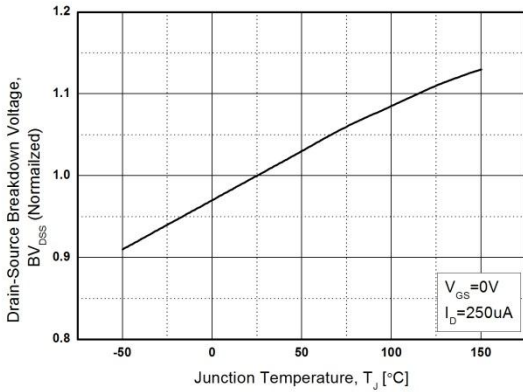


Fig. 8. Static on-Resistance vs. Temperature

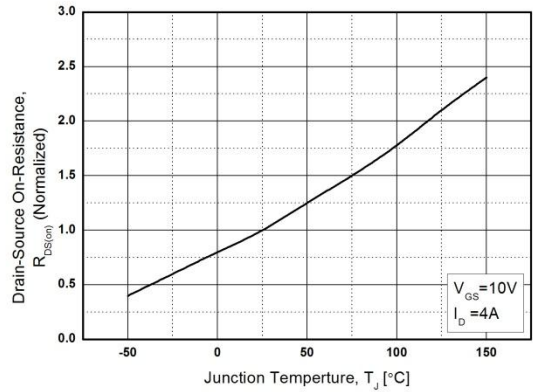


Fig. 9. Maximum Safe Operating Area

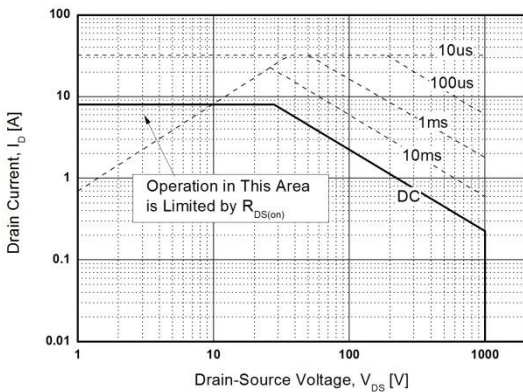


Fig. 10. Maximum Drain Current vs. Temperature

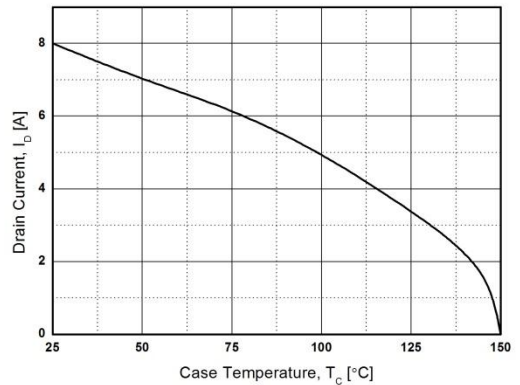
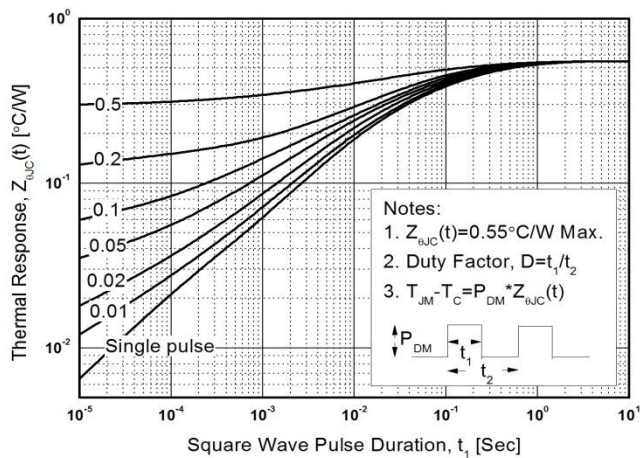


Fig. 11. Transient Thermal Response Curve



Package Dimensions

TO-3PN

(Dimensions in Millimeters)

